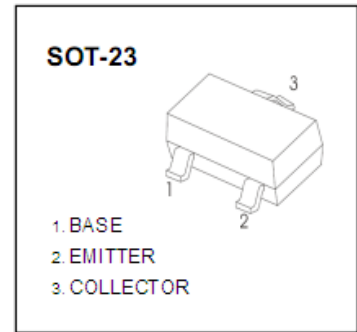


**2SA812 (PNP)****特点/Features :**

- 1、 h_{FE} 高, $h_{FE}=200(\text{TYP})$ $V_{CE}=-6\text{V}, I_C=-1\text{mA}$;
- 2、高电压, $V_{CEO}=-50\text{V}$;

用途/Applications :

用于一般放大, 与 2SC1623 互补。

**极限参数/Absolute maximum ratings($T_a=25^\circ\text{C}$)**

参数/Parameter	符号/ Symbol	数值/Value	单位/Unit
集电极-基极电压/Collector-Base Voltage	V_{CB0}	-60	V
集电极-发射极电压/Collector-Emitter Voltage	V_{CEO}	-50	V
发射极-基极电压/Emitter-Base Voltage	V_{EB0}	-5	V
集电极连续电流/Collector Current Continuous	I_C	-0.1	A
集电极耗散功率/Collector Power Dissipation	P_C	0.2	W
结温/Junction Temperature	T_j	150	$^\circ\text{C}$
储存温度/Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$

电性能参数/Electrical characteristics ($T_a=25^\circ\text{C}$)

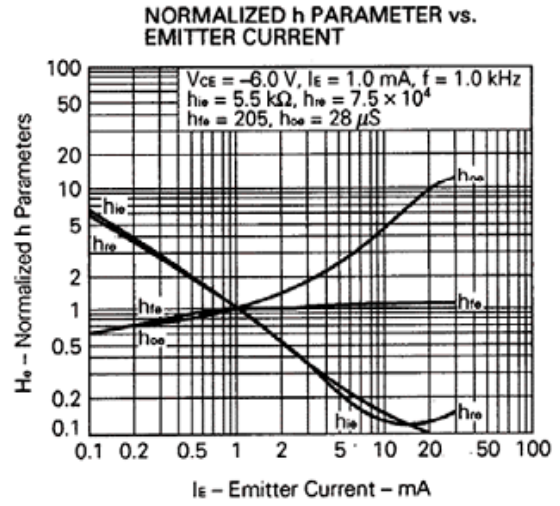
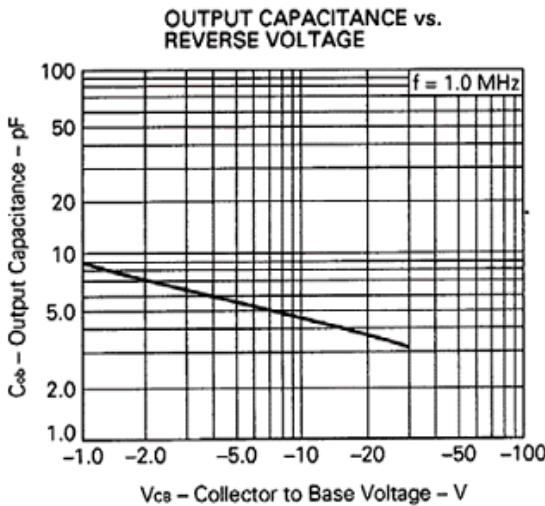
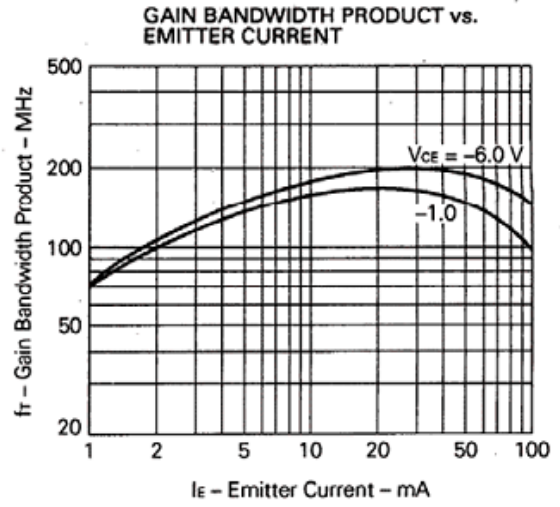
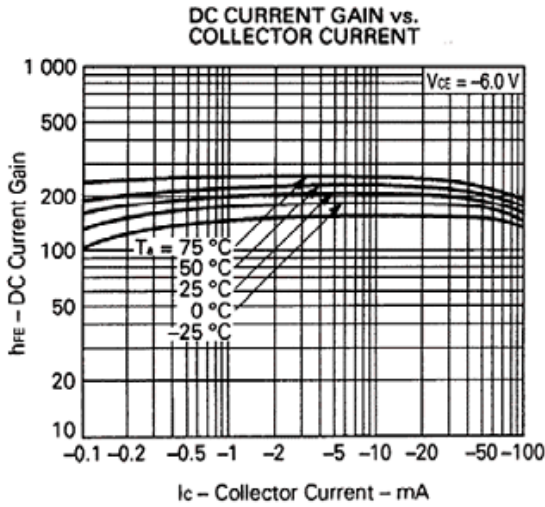
参数	符号	测试条件	最小值	典型值	最大值	单位
集电极-基极击穿电压	$V_{BR(CB0)}$	$I_C=-100\ \mu\text{A}, I_E=0$	-60			V
集电极-发射极击穿电压	$V_{BR(CEO)}$	$I_C=-1\text{mA}, I_B=0$	-50			V
发射极-基极击穿电压	$V_{BR(EB0)}$	$I_E=-100\ \mu\text{A}, I_C=0$	-5			V
集电极截止电流	I_{CB0}	$V_{CB}=-60\text{V}, I_E=0$			-0.1	μA
发射极截止电流	I_{EB0}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
直流电流增益	h_{FE}	$V_{CE}=-6\text{V}, I_C=-1\text{mA}$	90		600	
集电极-发射极饱和压降	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_B=-10\text{mA}$			-0.3	V
基极-发射极饱和压降	V_{BE}	$I_C=-1\text{mA}, V_{CE}=-6\text{V}$	-0.58		-0.68	V
特征频率	f_T	$V_{CE}=-6\text{V}, I_C=-10\text{mA}$		180		MHz
集电极输出电容	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=10\text{MHz}$		4.5		pF

印章/Marking & h_{FE} 分档/Classification of h_{FE}

范围/Range	90~180	135~270	200~400	300~600
印章/Marking	M4	M5	M6	M7



典型特性曲线图/Typical Characteristics



NORMALIZED h PARAMETER vs. COLLECTOR TO EMITTER VOLTAGE

NORMALIZED h PARAMETER vs. COLLECTOR TO EMITTER VOLTAGE

